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## Correction: Synergistic crucible design and thermal-flow management for enhanced 4-inch AlN single crystal PVT growth: a combined numerical and experimental investigation

Wenliang Li, <sup>ab</sup> QianLing Liu,<sup>ab</sup> Jun Tan,<sup>ab</sup> Guangze He,<sup>ab</sup> Yingmin Wang,<sup>cd</sup> Zhenhua Sun, <sup>ab</sup> Baikui Li <sup>ab</sup> and Honglei Wu <sup>\*ab</sup>

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Correction for 'Synergistic crucible design and thermal-flow management for enhanced 4-inch AlN single crystal PVT growth: a combined numerical and experimental investigation' by Wenliang Li et al., *CrystEngComm*, 2025, 27, 3219–3228, <https://doi.org/10.1039/D5CE00214A>.

In the originally published version of this manuscript, the ORCID iD for Zhenhua Sun was incorrect. The correct ORCID iD is: **0000-0002-9227-6738**, and is now accurately listed above in this corrigendum.

Furthermore, the caption for Fig. 6 contained an error in the description of panels b and c. The correct caption for Fig. 6 is shown below.

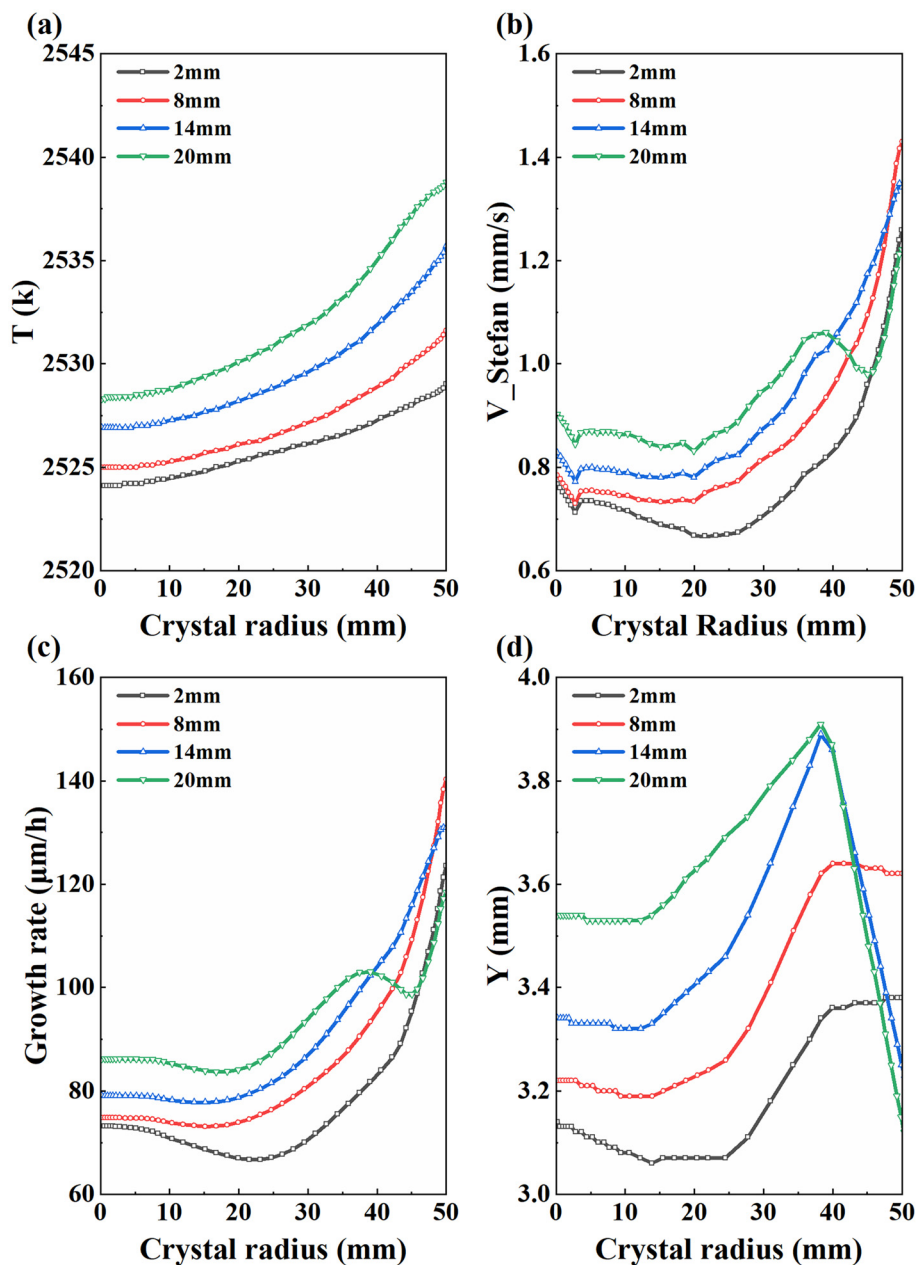
<sup>a</sup> State Key Laboratory of Radio Frequency Heterogeneous Integration (Shenzhen University), College of Physics and Optoelectronic Engineering, Shenzhen University, Shenzhen, 518060, China. E-mail: hlvu@szu.edu.cn

<sup>b</sup> Key Laboratory of Optoelectronic Devices and Systems of Ministry of Education and Guangdong Province, College of Physics and Optoelectronic Engineering, Shenzhen University, Shenzhen, 518060, China

<sup>c</sup> The 46th Research Institute, China Electronics Technology Group Corporation, Tianjin, 300220, China

<sup>d</sup> Key Laboratory of Advanced Semiconductor Materials of CTEC, Tianjin, 300220, China





**Fig. 6** Simulation of crystal growth states with different distances between the material and the side-wall: (a) temperature distribution at the seed crystal position, (b) situation of the Stefan flow at the seed crystal position in the initial stage, (c) growth rate during the stage at 30 hours of crystal growth, (d) results of seed crystal growth for 30 h at different distances from the material surface.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

